1. General description

PNP high-voltage low V_{CEsat} transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability $\rm I_{C}$ and $\rm I_{CM}$
- High collector current gain (h_{FE}) at high I_C
- Medium power SMD plastic package
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Electronic ballasts
- · LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Flyback converters
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	-	-500	V
V_{CEO}	collector-emitter voltage	open base	-	-	-500	V
I _C	collector current		-	-	-0.25	Α
h _{FE}	DC current gain	V_{CE} = -10 V; I_{C} = -50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	80	160	300	



500 V, 250 mA PNP high-voltage low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C
2	С	collector		В
3	E	emitter		D —
4	С	collector	□ 1 □ 2 □ 3	Ė
			SC-73 (SOT223)	sym028

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PBHV9050Z-Q	SC-73	plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223				

7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV9050Z-Q	V9050Z

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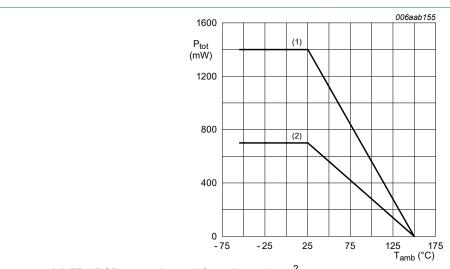
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-500	V
V _{CEO}	collector-emitter voltage	open base		-	-500	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	-500	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-0.25	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-0.5	Α
I _{BM}	peak base current			-	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	700	mW
			[2]	-	1400	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

500 V, 250 mA PNP high-voltage low VCEsat transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	-	175	K/W
junction to am	junction to ambient		[2]	-	-	90	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

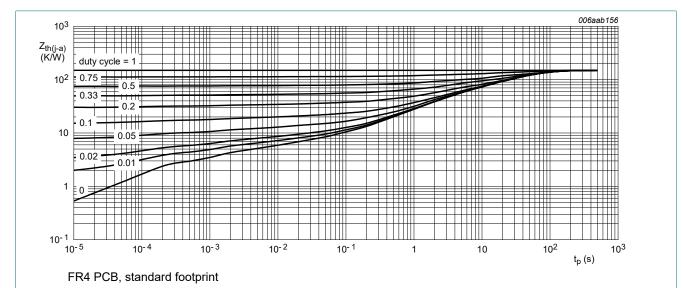


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

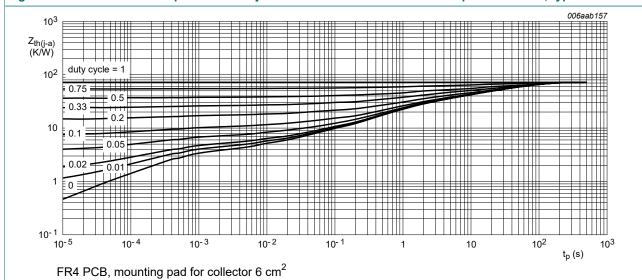


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

500 V, 250 mA PNP high-voltage low VCEsat transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -360 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -360 V; I _E = 0 A; T _j = 150 °C	-	-	-10	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = -360 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -10 V; I_{C} = -10 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	160	300	
		V_{CE} = -10 V; I_{C} = -50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	80	160	300	
		V_{CE} = -10 V; I_{C} = -100 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	70	150	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -20 mA; I_B = -2 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-115	-200	mV
		I_C = -50 mA; I_B = -10 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-95	-200	mV
		I_C = -100 mA; I_B = -20 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-140	-350	mV
V _{BEsat}	base-emitter saturation voltage	I_C = -50 mA; I_B = -10 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-0.75	-0.9	V
t _d	delay time	V_{CC} = -20 V; I_{C} = -0.05 A; I_{Bon} = -5 mA;	-	75	-	ns
t _r	rise time	I _{Boff} = 10 mA; T _{amb} = 25 °C	-	1600	-	ns
t _{on}	turn-on time		-	1675	-	ns
t _s	storage time		-	1200	-	ns
t _f	fall time		-	550	-	ns
t _{off}	turn-off time		-	1750	-	ns
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	-	50	-	MHz
C _c	collector capacitance	$V_{CB} = -20 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 ^{\circ}\text{C}$	-	6	-	pF
C _e	emitter capacitance	V_{EB} = -0.5 V; I_{C} = 0 A; i_{c} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	170	-	pF

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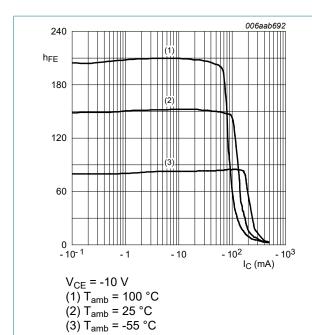


Fig. 4. DC current gain as a function of collector current; typical values

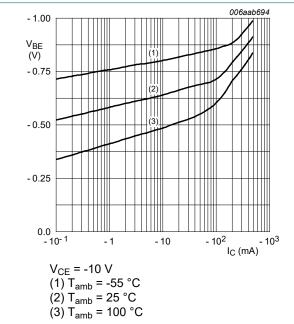


Fig. 6. Base-emitter voltage as a function of collector current; typical values

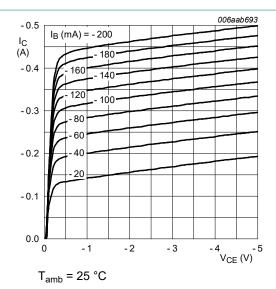
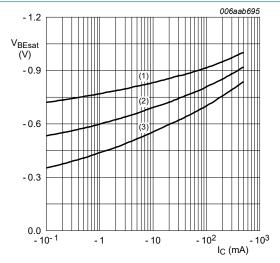


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $I_{\rm C}/I_{\rm B}=5$

(1) $T_{amb} = -55$ °C

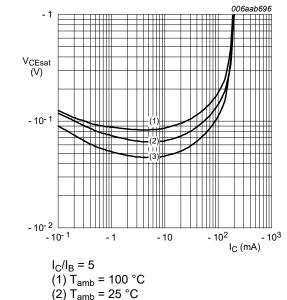
(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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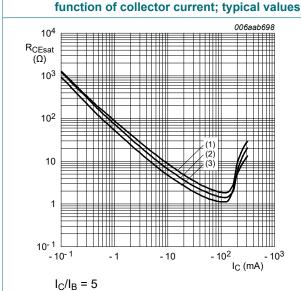
500 V, 250 mA PNP high-voltage low VCEsat transistor



(1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -55 °C

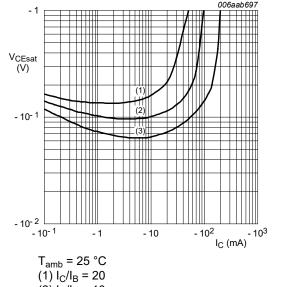
Fig. 8.

Collector-emitter saturation voltage as a



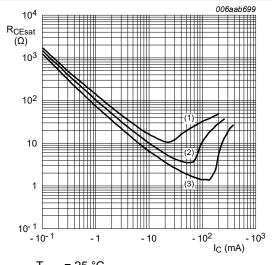
(1) $T_{amb} = 100 \, ^{\circ}C$ (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



(2) $I_C/I_B = 10$ (3) $I_C/I_B = 5$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

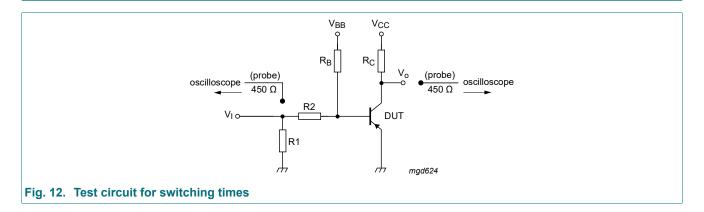


 T_{amb} = 25 °C $(1) I_{\rm C}/I_{\rm B} = 20$ $(2) I_{\rm C}/I_{\rm B} = 10$ (3) $I_C/I_B = 5$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

500 V, 250 mA PNP high-voltage low VCEsat transistor

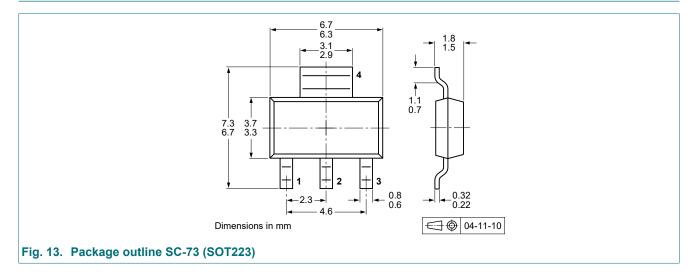
11. Test information



Quality information

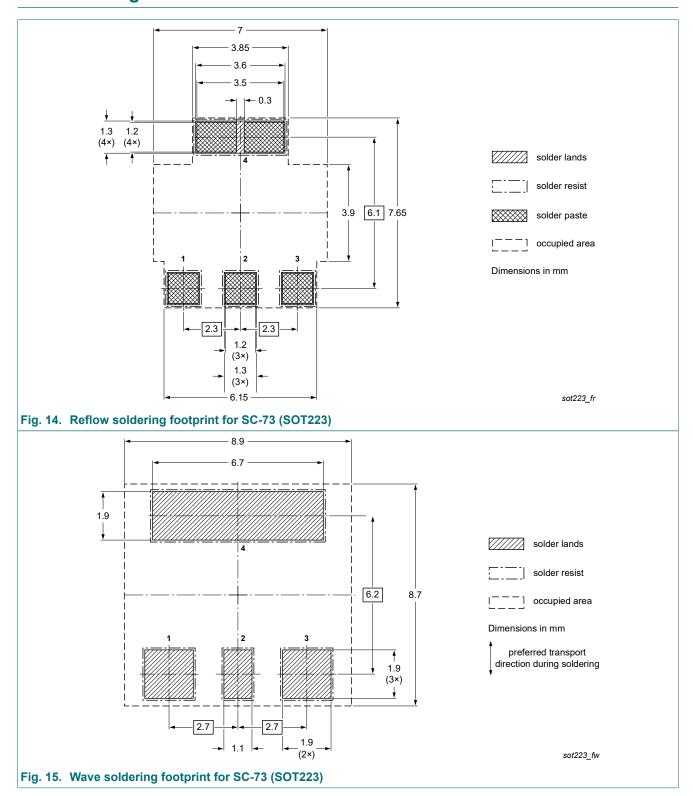
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



500 V, 250 mA PNP high-voltage low VCEsat transistor

13. Soldering



500 V, 250 mA PNP high-voltage low VCEsat transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9050Z-Q v.1	20230717	Product data sheet	-	-

500 V, 250 mA PNP high-voltage low VCEsat transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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PBHV9050Z-Q

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